

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	16923	324/207.2,207.21,249,251,252.ccls. 338/32R,32H.ccls. 438/3,14,17.ccls. 29/592, 591.1,602.1,603.1,607.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 04:26
S2	415	S1 and spin near2 valve	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 04:29
S3	373	S2 and (substrate semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 04:30
S4	369	S3 and layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 04:30
S5	364	S4 and (magnet\$2 near2 resist\$3 magneto\$1resist\$4 gmr tmr)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 06:41
S6	6723	spin near2 valve	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 04:30
S7	3966	S6 and (substrate semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 04:30

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S8	1958	S7 and (pinned near3 layer) and (free near3 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 04:30
S9	1917	S8 and (magnet\$2 near2 resist\$3 magneto\$1resist\$4 gmr tmr)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 04:31
S12	16923	324/207.2,207.21,249,251,252.ccls. 338/32R,32H.ccls. 438/3,14,17.ccls. 29/592, 591.1,602.1,603.1,607.ccls.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59
S13	415	S12 and spin near2 valve	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59
S14	373	S13 and (substrate semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59
S15	369	S14 and layer	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59
S16	364	S15 and (magnet\$2 near2 resist\$3 magneto\$1resist\$4 gmr tmr)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59

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S17	6723	spin near2 valve	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59
S18	3966	S17 and (substrate semiconductor)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59
S19	1958	S18 and (pinned near3 layer) and (free near3 layer)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59
S20	1917	S19 and (magnet\$2 near2 resist\$3 magneto\$1 resist\$4 gmr tmr)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59
S21	1740	S20 not S16	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2006/09/05 07:59